

CBH-35

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|---|---|
| 1. Color
2. Material
3. Electrode
4. Electrode pattern
5. Chip size
6. Electro-Optical characteristics (Ta = 25°C) | Infrared
AlGaAs/GaAs
N side (cathode): Au / P side (anode): Au
(Fig.)
0.325mm × 0.325mm × 0.280mmH (Fig.) |
|---|---|

Parameters	Symbol	Condition	Characteristics			Unit
			Min.	Typ.	Max.	
Power*	Po	IF = 20mA	0.7	1.1		mW
Forward Voltage	VF	IF = 20mA		1.70	1.90	V
Reverse Current	IR	VR = 5V			10	μA
Peak Wavelength	λP	IF = 20mA		770		nm
Spectral Radiation Bandwidth	Δλ	IF = 20mA		30		nm
Rise time	tr	IF = 20mA		25		ns
Fall time	tf	IF = 20mA		15		ns

* Power Measurement at RESONAC PHOTONICS.

LED chip : To be mounted on TO-18 gold header without resin coating.

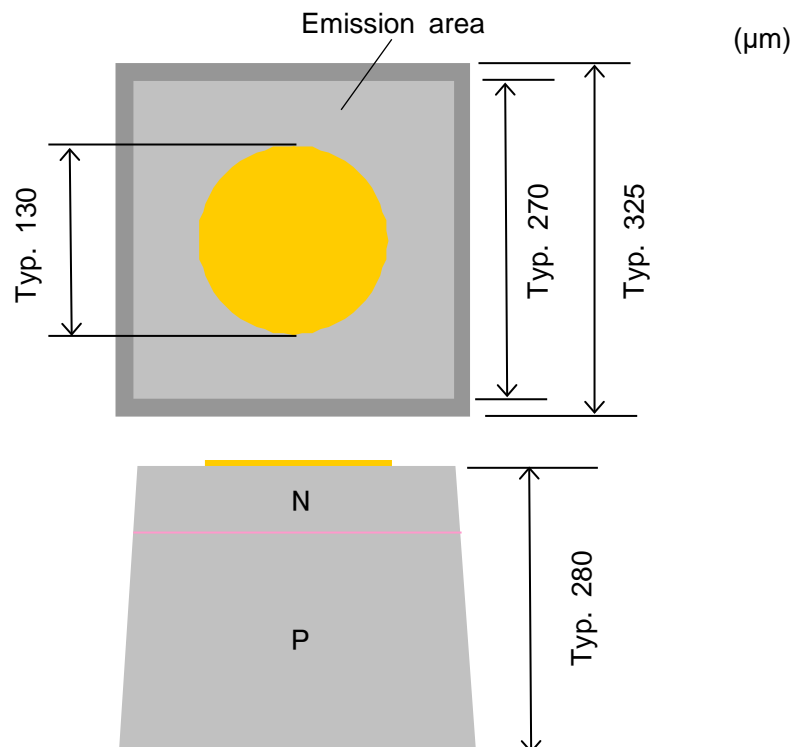


Fig. Electrode pattern & Chip size

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